

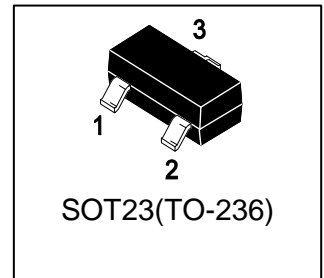
# LMBD2836LT1G

## S-LMBD2836LT1G

Monolithic Dual Switching Diodes

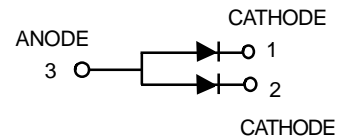
### 1. FEATURES

- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.



### 2. DEVICE MARKING AND RESISTOR VALUES

| Device       | Marking | Shipping        |
|--------------|---------|-----------------|
| LMBD2836LT1G | A2X     | 3000/Tape&Reel  |
| LMBD2836LT3G | A2X     | 10000/Tape&Reel |



### 3. MAXIMUM RATINGS(Ta = 25°C)

| Parameter                 | Symbol | Limits | Unit |
|---------------------------|--------|--------|------|
| Peak Reverse Voltage      | VRM    | 75     | V    |
| D.C Reverse Voltage       | VR     | 75     | V    |
| Peak Forward Current      | IFM    | 300    | mA   |
| Average Rectified Current | IO     | 100    | mA   |

### 4. THERMAL CHARACTERISTICS

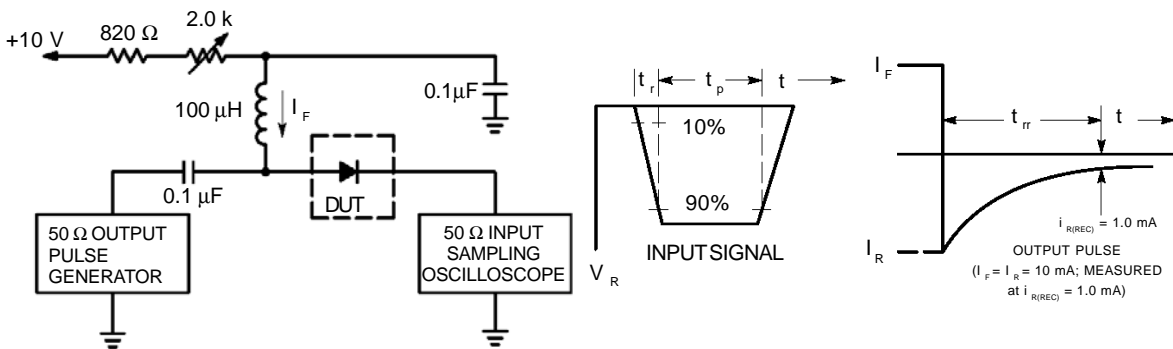
| Parameter  | Symbol    | Limits     | Unit        |
|--|-----------|------------|-------------|
| Total Device Dissipation FR- 5 Board, (Note 1)<br>TA = 25°C<br>Derate above 25°C       | PD        | 225<br>1.8 | mW<br>mW/°C |
| Thermal Resistance, Junction to Ambient  | RθJA      | 556        | °C/W        |
| Total Device Dissipation<br>Alumina Substrate, (Note 2) TA = 25°C<br>Derate above 25°C | PD        | 300<br>2.4 | mW<br>mW/°C |
| Thermal Resistance, Junction to Ambient  | RθJA      | 417        | °C/W        |
| Junction and Storage Temperature   | TJ , Tstg | -55~+150   | °C          |

1. FR-5 = 1.0 x 0.75 x 0.062 in.

2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

**5. ELECTRICAL CHARACTERISTICS (Ta= 25°C)**

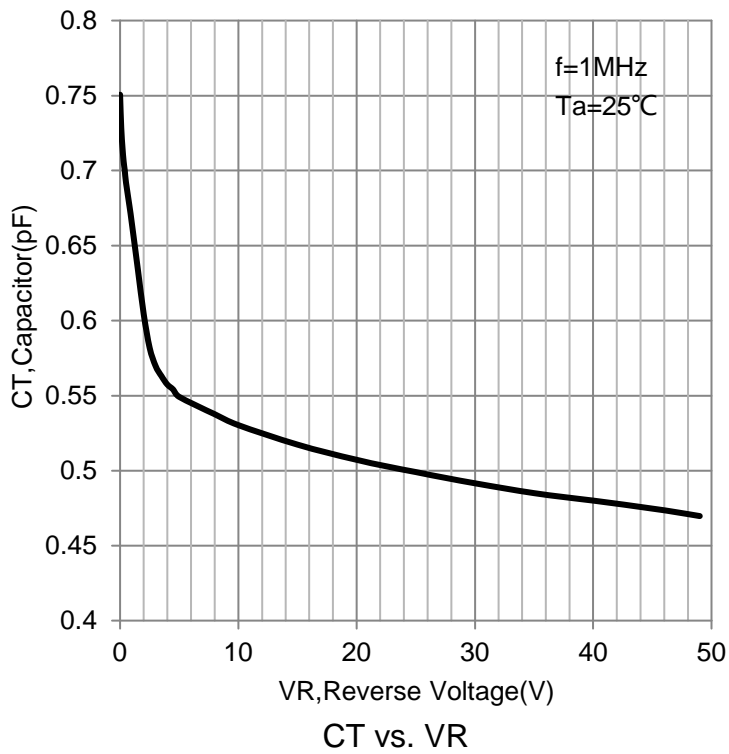
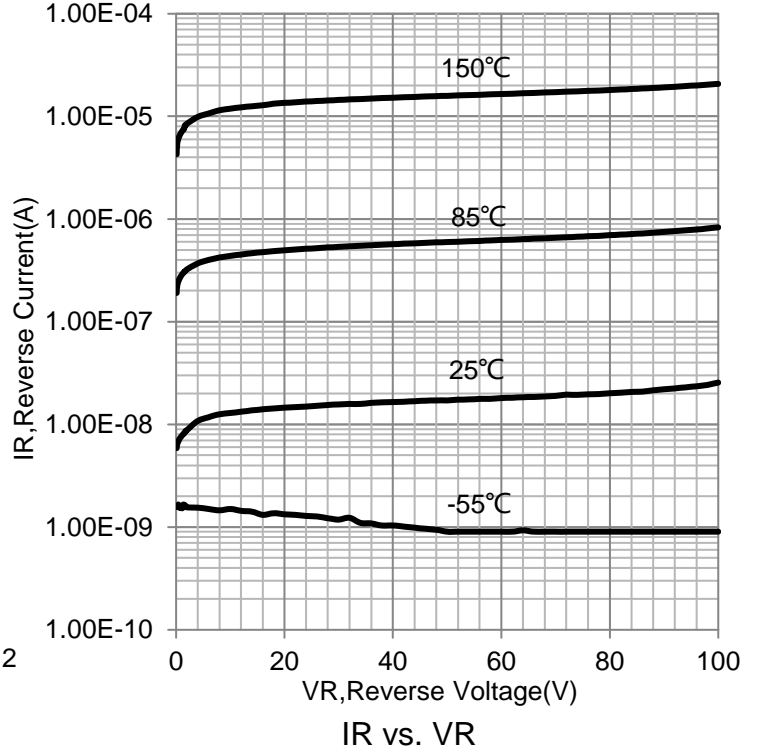
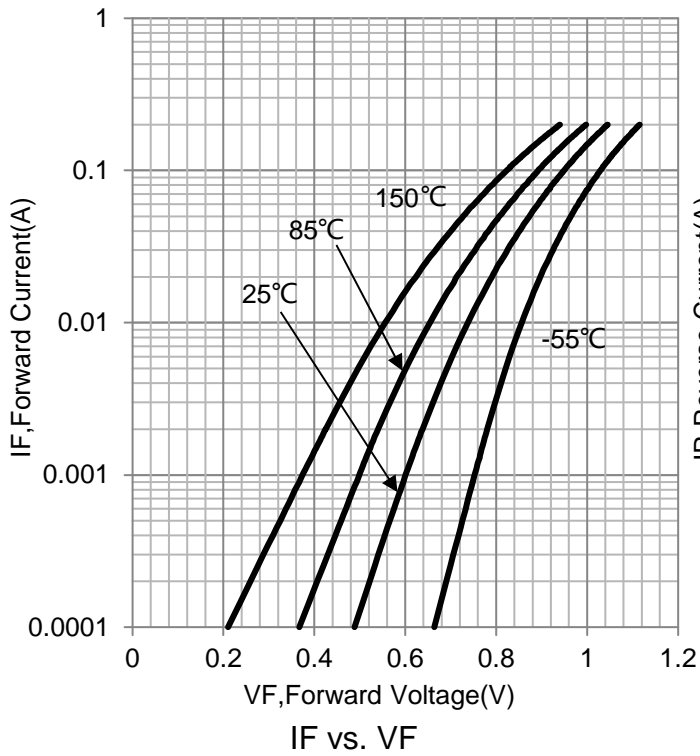
| CHARACTERISTICS  | Symbol | Min         | Max           | Unit |
|--|--------|-------------|---------------|------|
| Reverse Breakdown Voltage<br>(IBR = 100 μA)                            | VBR    | 75          | -             | V    |
| Reverse Voltage Leakage Current<br>(VR=50V)                            | IR     | -           | 100           | nA   |
| Diode capacitance<br>(VR = 0, f = 1.0 MHz)                             | CT     | -           | 4             | pF   |
| Forward voltage<br>(IF =10mA)<br>(IF =50mA)<br>(IF =100mA)             | VF     | -<br>-<br>- | 1<br>1<br>1.2 | V    |
| Reverse Recovery Time<br>(IF = IR = 10 mA, IR(REC) = 1.0mA) (Figure 1) | Trr    | -           | 4             | nS   |



- Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current ( $I_F$ ) of 10mA.
- 2. Input pulse is adjusted so  $I_{R(peak)}$  is equal to 10mA.
- 3.  $t_p \gg t_{rr}$

**Figure 1. Recovery Time Equivalent Test Circuit**

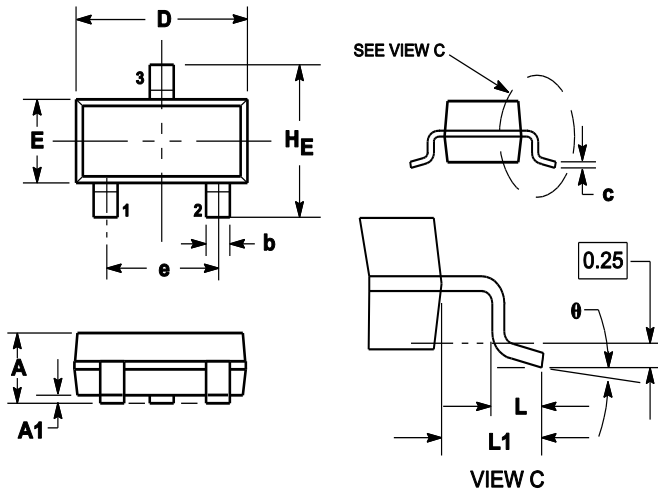
**6.ELECTRICAL CHARACTERISTICS CURVES**



### 7. OUTLINE AND DIMENSIONS

Notes:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.



| DIM | MILLIMETERS |      |      | INCHES |       |       |
|-----|-------------|------|------|--------|-------|-------|
|     | MIN         | NOM  | MAX  | MIN    | NOM   | MAX   |
| A   | 0.89        | 1    | 1.11 | 0.035  | 0.04  | 0.044 |
| A1  | 0.01        | 0.06 | 0.1  | 0.001  | 0.002 | 0.004 |
| b   | 0.37        | 0.44 | 0.5  | 0.015  | 0.018 | 0.02  |
| c   | 0.09        | 0.13 | 0.18 | 0.003  | 0.005 | 0.007 |
| D   | 2.80        | 2.9  | 3.04 | 0.11   | 0.114 | 0.12  |
| E   | 1.20        | 1.3  | 1.4  | 0.047  | 0.051 | 0.055 |
| e   | 1.78        | 1.9  | 2.04 | 0.07   | 0.075 | 0.081 |
| L   | 0.10        | 0.2  | 0.3  | 0.004  | 0.008 | 0.012 |
| L1  | 0.35        | 0.54 | 0.69 | 0.014  | 0.021 | 0.029 |
| HE  | 2.10        | 2.4  | 2.64 | 0.083  | 0.094 | 0.104 |
| θ   | 0°          | ---  | 10°  | 0°     | ---   | 10°   |

### 8. SOLDERING FOOTPRINT

